Microelectronics
Circuit Analysis and Design

Donald A. Neamen

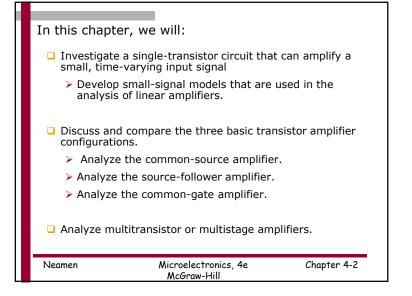
Chapter 4

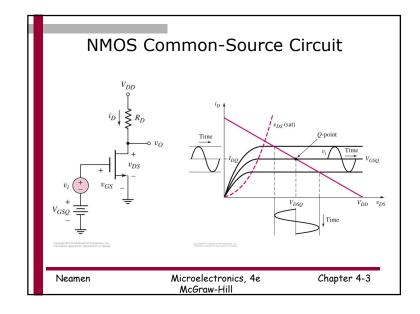
Basic FET Amplifiers

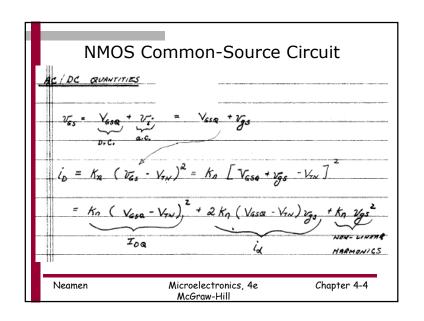
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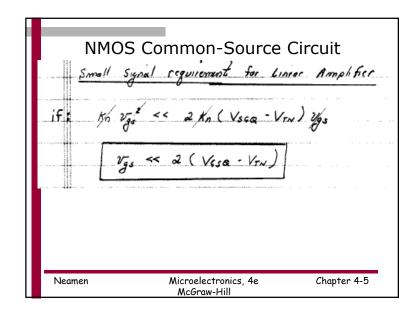
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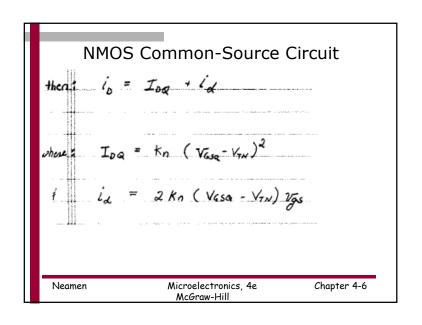
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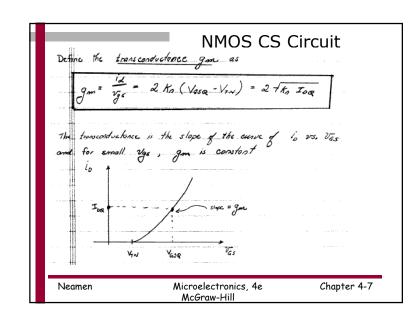


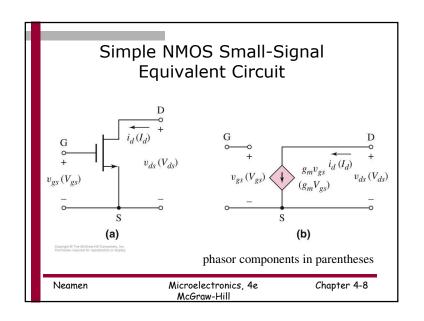












Simple NMOS Small-Signal Equivalent Circuit

Recall the slope in the MOSFET characteristic curve! The effect is that of drain to source resistance r.

$$\begin{split} r_o &= (\frac{\partial i_D}{\partial v_{DS}})^{-1} \\ r_o &= [\lambda K_n (V_{GSQ} - V_{TN})^2]^{-1} \cong [\lambda I_{DQ}]^{-1} \end{split}$$

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NMOS Transistor Small-Signal Parameters

■ Values depends on Q-point

$$g_{m} = \frac{\partial i_{D}}{\partial v_{GS}} = \frac{i_{d}}{v_{gS}}$$

$$g_{m} = 2K_{n}(V_{GSQ} - V_{TN}) = 2\sqrt{K_{n}I_{DQ}}$$

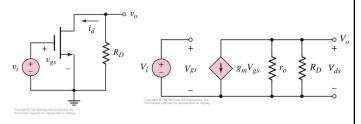
$$r_{o} = (\frac{\partial i_{D}}{\partial v_{DS}})^{-1}$$

$$r_{o} = [\lambda K_{n}(V_{GSQ} - V_{TN})^{2}]^{-1} \cong [\lambda I_{DQ}]^{-1}$$

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NMOS Common-Source Circuit



AC

Small-signal

$$A_{v} = V_{o}/V_{i} = -g_{m}(r_{o}||R_{D})$$

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Problem-Solving Technique: MOSFET AC Analysis

- 1. Analyze circuit with only the dc sources to find quiescent solution. Transistor must be biased in saturation region for linear amplifier.
- 2. Replace elements with small-signal model.
- 3. Analyze small-signal equivalent circuit, setting dc sources to zero, to produce the circuit to the time-varying input signals only.

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